

1. Number	2. Hits	3. Search Text	4. DB	5. Time stamp
1	1	"20030015740"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 14:36
2	13741	Jian Li.INV.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 14:37
3	14149	intel.AS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 14:37
4	64	intel.AS. and (Jian Li.INV.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 14:37
5	3	(intel.AS. and (Jian Li.INV.)) and topology	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 14:59
6	113555	memory adj device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 15:00
7	43429	bit adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 15:01
8	38458	word adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 15:04
9	10847	(memory adj device) and (bit adj line) and (word adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 15:16
10	27654	topology	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 15:52
11	2249	self-aligned adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 15:53
12	687	buried adj bit adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/11 15:54

13	35	(self-aligned adj contact) and (buried adj bit adj line)	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 16:23
14	5	((self-aligned adj contact) and (buried adj bit adj line)) and damascene	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 15:56
15	0	((self-aligned adj contact) and (buried adj bit adj line)) and (not 14.)	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 15:56
16	11	((self-aligned adj contact) and (buried adj bit adj line)) and CVD	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 17:43
17	2	"20020135027"	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 17:52
18	187537	seiko epson.AS.	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 17:53
19	37	(seiko epson.AS.) and drain-drain	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 17:53
20	33	((seiko epson.AS.) and drain-drain) and SRAM	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 18:16
21	27299	Thinh Nguyen.XA.	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 17:55
22	206	(Thinh Nguyen.XA.) and (seiko epson.AS.)	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 17:55
23	0	((Thinh Nguyen.XA.) and (seiko epson.AS.)) and drain-drain	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 17:56
24	90	((Thinh Nguyen.XA.) and (seiko epson.AS.)) and memory	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 17:58
25	1964803	Thinh T Nguyen XA	USPAT: US-PGPUB: EPO; JPO; DERWENT; IBM_TDB	2003/03/11 17:58

26	0	(Thinh adj nguyen).XA.	USPAT: 2003 03 11 17:59 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB
27	13	Thinh adj nguyen	USPAT: 2003 03 11 18:04 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB
28	320	Thinh.XA.	USPAT: 2003 03 11 18:00 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB
29	2	((Thinh Nguyen.XA.) and (seiko epson.AS.)) and memory) and Thinh.XA.	USPAT: 2003/03 11 18:01 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB
30	174054	257 \$.ccls.	USPAT: 2003/03/11 18:02 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB
32	0	(Thinh.XA. and (seiko epson.AS.)) and 257\$/ccls.	USPAT: 2003/03/11 18:02 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB
31	8	Thinh.XA. and (seiko epson.AS.)	USPAT: 2003/03/11 18:02 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB
33	0	Thinh adj T adj Nguyen	USPAT: 2003/03/11 18:04 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB
34	580	fourth adj conductive adj layer	USPAT: 2003/03/11 18:17 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB
35	61	(fourth adj conductive adj layer) and SRAM	USPAT: 2003/03/11 18:18 US-PGPUB: EPO; JPO; DERWENT: IBM_TDB